

MICRO ELECTRONICS

2SK19

N-CHANNEL
SILICON
FET

DESCRIPTION

2SK19 is N-channel silicon planar field effect transistor designed for FM tuner and VHF amplifier applications.

CASE TO-92DD



ABSOLUTE MAXIMUM RATINGS

Gain-Drain Voltage	VGDO	-18V
Gate Current	IG	10mA
Total Power Dissipation @ Ta=25°C	Ptot	200mW
Operating & Storage Junction Temperature	Tj, Tstg	-55 to +125°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Gate-Drain Breakdown Voltage	BVGDO	-18			V	IG=-100µA
Gate Reverse Current	IGSS			-10	nA	VGS=-1V VDS=0
Zero-Gate Voltage Drain Current	IDSS *	3		24	mA	VDS=10V VGS=0
Gate-Source Cutoff Voltage	VGS(off)	-1.2	-3		V	VDS=10V ID=1µA
Forward Transadmittance	yfs		5.5		mU	VDS=10V VGS=0 f=1kHz
Reverse Transfer Capacitance	Crss		0.45	0.65	pF	VGD=-10V f=1MHz

* According to the value of IDSS, 2SK19 is classified as follows.

2SK19-Y : 3-7

2SK19-GR : 6-14

2SK19-BL : 12-24



MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.

Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5